

IN THE SPECIFICATION:

Please amend the paragraph beginning at page 3, line 19, as follows:

For example, Shimoda et al. fabricated an FET including an insulating layer made of polyvinyl phenol (PVP) and electrodes and an organic semiconductor layer all of which were formed by ink jet printing (refer to Shimoda, et al., "Organic Transistor Manufactured by Ink Jet Printing", ~~Appl. Phys. Lett.~~ Oyo Buturi, vol. 70, pp. 1452 (2001)). Meanwhile, Veres B .J., et al. fabricated an FET including an organic semiconductor layer made of polytriallylamine formed on an insulating layer having a low dielectric constant (refer to Veres B. J., et al., "Low-k insulator as the choice of dielectrics in organic field-effect transistors", vol. 13, pp. 199 (2003)). Since a thermoplastic resin is used as a material for forming the insulating layer in both of the above prior arts, the obtained FET's have high processability but involve problems with solvent resistance and heat stability. Therefore, they are not suitable for forming multiple layers and it has been difficult to form a thin layer showing sufficiently high insulating properties.